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340-81

10/686.519

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KOCHERGIN ET AL.

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FILING DATE

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16 October 2003

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U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

DOCUMENT	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	NO
400	3717851	Germany	—	—		
400	4202454	Germany	—	—		

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

DIA	Lehmann et al., Optical shortpass filters based on macroporous silicon <i>Appl. Phys. Lett.</i> V 78, N.5, Jan. 2001.
DEV	J. Schilling et al., "Three-dimensional photonic crystals based on Macroporous silicon with modulated pore diameter", <i>Appl. Phys. Lett.</i> V 78, N.9, Feb. 2001
DIA	S. Iizuo et al., "A novel electrochemical etching technique for n-type silicon," <i>Sensors and Actuators A</i> 97-98 (2002), pp. 720-724 (no month)
DEV	A. Vyatkin et al., "Random and Ordered Macropore Formation in p-Type Silicon," <i>J. of the Electrochem. Soc.</i> , 149 (1), pp. G70-G76 (2002) (no month)
DEV	H. Föll et. al, "Formation and application of porous silicon", <i>Mat. Sci. Eng. R</i> 39 (2002), pp. 93-141. (no month)
DIA	S. Langa et al., "Observation of crossing pores in anodically etched n-GaAs," <i>Appl. Phys. Lett.</i> 78(8), pp.1074- 1076, (2001). (no month)
DIA	H H. Föll et al., "Porous III-V compound semiconductors: formation, properties, and comparison to silicon", <i>Phys. Stat. Sol. A</i> , 197 (1), pp. 61-70 (2003) (no month)
DEV	M. Christphersen et al., "A comparison of pores in silicon and pores in III-V compound materials", <i>Phys. Stat. Sol. A</i> , 197 (1), pp. 197-203, (2003) (no month)
DIA	H. Föll et al., "Pores in III-V Semiconductors", <i>Adv. Materials, Review</i> , 2003, 15, pp.183 - 198, (2003) (no month)
DEV	S. Langa et al., <i>Phys. Stat. Sol. A</i> , 197 (1), p. 77, (2003) "Single crystalline 2D porous arrays obtained by self organization in n-InP" (pp. 77-82) (no month)

*Examiner

Donald R. Valentine

Date Considered

8-6-04

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DRV	K. Barla et al., "X-Ray Topographic Characterization of Porous Silicon Layers," <i>J. Cryst. Growth</i> , 68 , North-Holland, Amsterdam, p. 721-726 (1984)
DRW	B.H. Erne et al., "Porous Etching: A Means to Enhance the Photo response of Indirect Semiconductors," <i>Adv. Mater.</i> , 7 , p. 739-742 (1995)
DRV	P.A. Kohl et al., <i>J. Electrochem. Soc.</i> , 130 (111), "The Photoelectrochemical Oxidation of (100), (111), and (111) n-InP and n-GaAs," p. 2288-2293 (11/1983)
DRV	Schmuki P. et al., <i>Physica Status Solidi A</i> , "Pore Formation on n-InP," 182 (1), pp. 51-61, (2000)
DRW	S. Langa et al., "Formation of Porous Layers with Different Morphologies during Anodic Etching of n-InP," <i>J. Electrochem. Soc. Lett.</i> , 3 (11), p. 514-516, (2000).
DRW	S. Langa et al., <i>Phys. Stat. Sol. (A)</i> , 195 (3), "Electrochemical pore etching in Ge," R4-R6 (2003)
DRW	Macleod H.A., <i>Thin-Film Optical Filters</i> , 3rd ed., Institute of Physics Publishing, 2001
DRW	D.J. Lockwood et al., "Optical properties of porous GaAs," <i>Physica E</i> , 4 , pp. 102-110 (1999)
DRW	Schmulki, P. et al., "Formation of porous layers on InSb(100) by anodization," <i>Phys. Stat. Sol. (a)</i> 197 , No. 1, pp. 71-76 (2003)
DRW	Langa, S. et al., "Voltage oscillations – an emergent property at high density pore growth," <i>Phys. Stat. Sol. (a)</i> 197 , No. 1, pp. 186-191 (2003)

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